

7A, 6.5V, 1MHz, ACOT[®] Synchronous Step-Down Converter with I²C Interface

General Description

The RT5757A is a high-performance, synchronous step-down DC-DC converter that can deliver up to 7A output current from a 3V to 6.5V input supply. The output voltage is programmable from 0.6V to 1.725V with I²C controlled 7-bit VID.

The device integrates low $R_{DS(ON)}$ power MOSFETs, accurate 0.6V reference and an integrated diode of bootstrap circuit to offer a very compact solution.

The RT5757A adopts Advanced Constant On-Time (ACOT®) control architecture that provides ultrafast transient response and further reduces the external-component count. In steady states, the ACOT® operates at nearly constant switching frequency over line, load and output voltage ranges and makes the EMI filter design easier. The RT5757A offers automatic PSM that maintains high efficiency during light load operation. The RT5757A can also operate in Forced-CCM through I²C setting that helps meet tight voltage regulation accuracy requirements.

The device offers a variety of functions for more design flexibility. The switching frequency, current limit level and over-temperature threshold are selectable via I²C. Independent enable control input pin and power good indicator are also provided for easy sequence control. Besides, the designer can also enable or shutdown the device via the I²C interface.

The device offers independent enable control input pin and power good indicator for easy sequence control. To control the inrush current during the startup, the device provides a programmable soft-start up by an external capacitor connected to the SS pin. Full protection features are also integrated in the device, including the cycle-by-cycle current limit control, UVP, input UVLO and OTP.

The RT5757A is available in a thermally enhanced UQFN-13L 3x3 (FC) package.

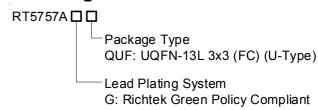
Features

- Dramatically Fast Transient Response
- Steady 1MHz ±20% Switching Frequency
- Advanced COT Control Loop
- Optimized for Ceramic Output Capacitors
- 3V to 6.5V Input Voltage Range
- Integrated $12m\Omega/8m\Omega$ MOSFETs
- Internal Start-Up into Pre-Biased Outputs
- Power Good Indicator
- Enable Control
- Over-Current and Over-Temperature Protections
- Under-Voltage Protection with Hiccup Mode
- VID Control Range Via I²C Compatible Interface : 0.6V to 1.725V step = 12.5mV
- Junction Temperature Range : -40°C to 125°C
- Ambient Temperature Range : -40°C to 85°C

Applications

- Mobile Phones and Handheld Devices
- STB, Cable Modem, and xDSL Platform
- WLANASIC Power / Storage (SSD and HDD)
- General Purpose for POL LV Buck Converter
- TV

Ordering Information

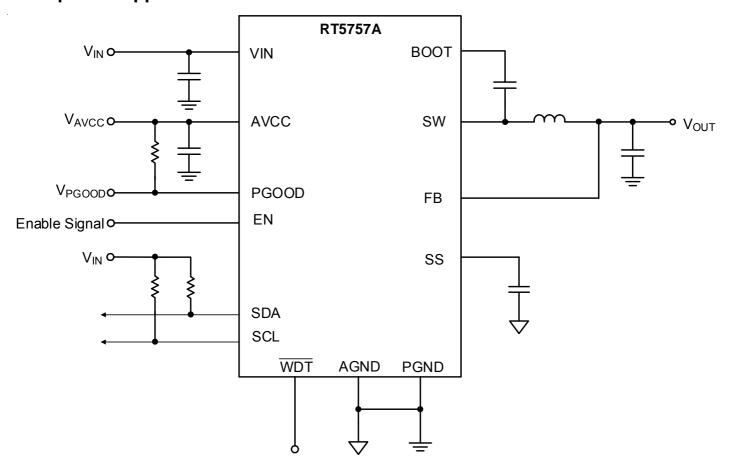


Note:

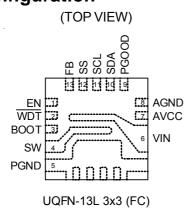
Richtek products are Richtek Green Policy compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.



Simplified Application Circuit



Pin Configuration



Marking Information



UY=: Product Code
YMDNN: Date Code

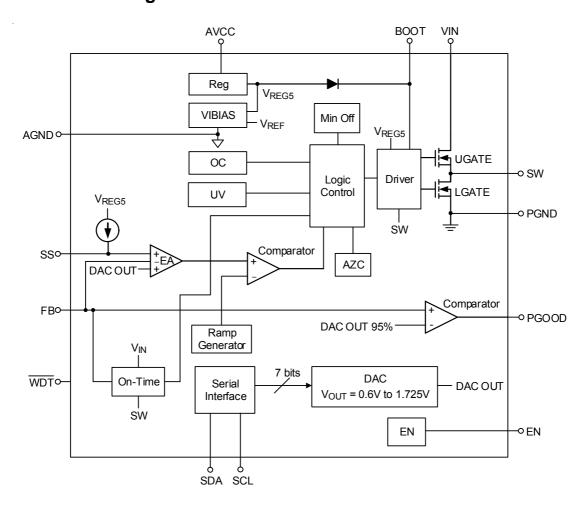


Functional Pin Description

Pin No.	Pin Name	Pin Function
1	EN	Enable control input. A logic-high enables the converter; a logic-low forces the IC into shutdown mode and reduces the supply current.
2	WDT	Control input for output voltage reset. Reset the output voltage register 0x02 to factory default setting value when this pin is pulled low. "Do Not" leave this pin floating.
3	воот	Bootstrap, supply for high-side gate driver. Connect a $0.1\mu F$ ceramic capacitor between BOOT and the SW pins.
4	SW	Switch node. Connect this pin to an external L-C filter.
5	PGND	System GND. The power GND of the controller circuit. Use wide PCB traces to make the connections.
6	VIN	Input voltage. Support 3V to 6.5V input voltage. Connect this pin with a suitable capacitance for noise decoupling. The bypass capacitor should be placed as close to the VIN pin as possible.
7	AVCC	LDO output for internal analog power. Connect a 4.7 μF capacitor as close to the VCC pin as possible.
8	AGND	Analog GND. AGND and PGND are connected with a short trace and at only one point to reduce circulating currents.
9	PGOOD	Power good indicator output. This pin has an open-drain structure. Pull this pin high to a voltage source with a $100 \text{k}\Omega$ resistor.
10	SDA	I ² C interface, DATA.
11	SCL	I ² C interface, CLK.
12	SS	Soft-start time control pin. Connect a capacitor between the SS pin and AGND to set the soft-start time. The default internal start-up time is 1.2ms without external capacitor.
13	FB	Feedback input. The pin is used to set the output voltage of the converter via a resistor divider. I ² C interface.



Functional Block Diagram



RT5757A



Operation

The RT5757A is a low voltage synchronous step-down converter that can support input voltage ranging from 3V to 6.5V and the output current can be up to 7A. The RT5757A uses ACOT® mode control. To achieve good stability with low-ESR ceramic capacitors, the ACOT® architecture uses a virtual inductor current ramp generated inside the IC.

This internal ramp signal replaces the ESR ramp normally provided by the output capacitor's ESR. The ramp signal and other internal compensations are optimized for low-ESR ceramic output capacitors. In steady-state operation, the feedback voltage, with the virtual inductor current ramp added, is compared with the reference voltage. When the combined signal is less than the reference, the on-time one-shot is triggered, as long as the minimum off-time one-shot is clear and the measured inductor current (through the synchronous rectifier) is below the current limit. The on-time one-shot turns on the high-side switch and the inductor current ramps up linearly. After the ontime, the high-side switch is turned off and the synchronous rectifier is turned on and the inductor current ramps down linearly. At the same time, the minimum off-time one-shot is triggered to prevent another immediate on-time during the noisy switching time and allows the feedback voltage and current sense signals to settle. The minimum off-time is kept short so that rapidly-repeated on-times can raise the inductor current quickly when needed.

Shutdown, Start-Up and Enable (EN)

The enable input (EN) has a logic-low level of 0.74V. When V_{EN} is below this level, the IC enters shutdown mode and supply current drops to less than 1 μ A. When V_{EN} exceeds its logic-high level of 0.92V, the IC is fully operational. When V_{EN} exceeds its logic-high level, the pre-regulator turns on first. The power-up sequence from EN logic high to PGOOD going high is shown in Figure 1.

Undervoltage Protection (UVLO)

The UVLO continuously monitors the AVCC voltage to make sure the device works properly. When the AVCC is high enough to reach the UVLO high threshold voltage, the step-down converter softly starts or pre-bias to its regulated output voltage. When the AVCC decreases to

its low threshold voltage, the device shuts down.

Power Good

Power Good pin is an open-drain logic output that is pulled to ground when the output voltage is lower or higher than its specified threshold under the conditions of OVP, OTP, dropout, EN shutdown, or during start-up time. Start-up time is the time of V_{OUT} soft-start when power up or enable up. During the start-up time, PGOOD is low even the output voltage is within the specified threshold voltage. Only when the PGOOD indicator is high and output voltage is within the specified threshold voltage, then PGOOD is high.

External Bootstrap Capacitor (CBOOT)

Connect a $0.1\mu F$ low ESR ceramic capacitor between BOOT and SW. This bootstrap capacitor provides the gate driver supply voltage for the high-side N-MOSFET switch.

Output Undervoltage Protection (UVP)

When the output voltage is lower than 70% reference voltage after soft-start, the UVP is triggered.

Over-Temperature Protection (OTP)

The RT5757A includes an Over-Temperature Protection (OTP) circuitry to prevent overheating due to excessive power dissipation. The OTP will shut down switching operation when the junction temperature exceeds 150°C. Once the junction temperature cools down and returns to 100°C, the IC will resume normal operation with a complete soft-start. For continuous operation, provide adequate cooling so that the junction temperature does not exceed 150°C.

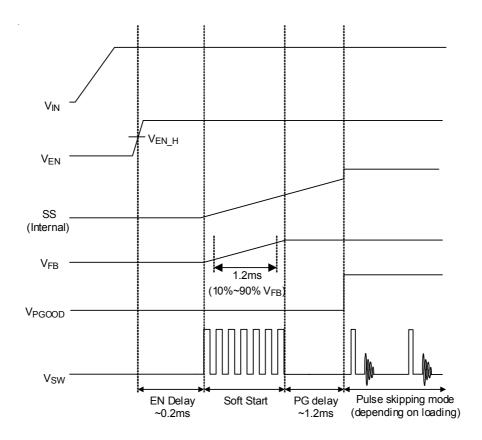


Figure 1. Power-Up Sequence Following Internal Soft-Start



Absolute Maximum Ratings (Note 1)

Supply Input Voltage, VIN	
Switch Node Voltage, SW	0.3V to 7V
SW (t ≤ 10ns)	–3V to 8.5V
• Boot Voltage, BOOT	–0.3V to 13V
• BOOT to SW (BOOT – SW)	0.3V to 6V
Other Pins Voltage	0.3V to 6V
 Power Dissipation, P_D @ T_A = 25°C 	
UQFN-13L 3x3 (FC)	2.62W
Package Thermal Resistance (Note 2)	
UQFN-13L 3x3 (FC), θ_{JA}	38.1°C/W
UQFN-13L 3x3 (FC), θ_{JC}	4.1°C/W
Junction Temperature Range	150°C
• Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	–65°C to 150°C
ESD Susceptibility (Note 3)	
HBM (Human Body Model)	2kV
Pacammandad Operating Conditions (Note 4)	
Recommended Operating Conditions (Note 4)	
Supply Input Voltage, VIN	
Junction Temperature Range	–40°C to 125°C

• Ambient Temperature Range ----- -40°C to 85°C

Electrical Characteristics

 $(V_{IN} = 5V, T_A = 25^{\circ}C, unless otherwise specified)$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Supply Voltage						
Input Voltage	VIN		3		6.5	V
Supply Current						
Sleep Supply Current	IQ	V _{FB} > 0.6V			100	μΑ
Shutdown Supply Current	Ishdn	V _{EN} = 0V			1	μΑ
UVLO	1					
UVLO Rising Threshold	V _{UVLO_R}	V _{AVCC} rising		2.625	2.8	V
UVLO Falling Threshold	Vuvlo_f	V _{AVCC} falling		2.5		V
Logic Threshold						
EN Input Rising Threshold	V _{ENH}		0.77	0.92	1.07	V
EN Input Falling Threshold	V _{ENL}		0.58	0.74	0.9	V
EN Hysteresis	ΔVEN			0.18		V
Input Current	I _{EN}	V _{EN} = 2V		1	5	μΑ



Parameter		Symbol	Test Conditions	Min	Тур	Max	Unit
Thermal Shutde	own					•	I.
Thermal Shutdo Threshold	wn	T _{SD}			150		°C
Thermal Recove Threshold	ery	T _{RC}			100		°C
Output Voltage	and Soft-St	art					
Output Voltage		Vout	ССМ	0.7425	0.75	0.7575	V
Soft-Start Time		tss	V _{OUT} = 0.75V, leave SS pin floating, 10% to 90%V _{OUT}		1.2		ms
R _{DS(ON)}							
Switch	High-Side	R _{DS(ON)} _H			12		
On-Resistance	Low-Side	RDS(ON)_L			8		mΩ
Current Limit						•	
Current Limit		I _{LIM}	Valley current	7.5	8.8	10.1	Α
Switching Freq	uency and M	/linimum Off-	Time				
Switching Frequ	ency	fsw	0x01[1:0] = 10b, CCM	0.8	1	1.2	MHz
Minimum Off-Tir	ne	toff_MIN			100		ns
Protections				•		•	l .
UVP Trip Thresh	nold	Vuvp			70		%
UVP Time Delay	/	tuvpdly			5		μS
Power Good							•
D000D D: :	-	V _{TH_PGLH}	V _{FB} rising (Good)		95		
PGOOD Rising	Inresnoia	ΔV _{TH_PGLH}	V _{FB} rising (Fault)		110		0/1/
D000D F III	-	VTH_PGHL	V _{FB} falling (Fault)		90		%V _{FB}
PGOOD Falling	Inreshold	ΔVTH_PGHL	V _{FB} falling (Good)		105		
PGOOD Enable	Delay Time		0x05 PGDSET[3:2] = 01b		10		μS
Discharge Resi	stor						
Discharge Resistor		RDISCHG	V _{EN} = 0V, V _{AVCC} = 5V		50		Ω
Regulation							
Line Regulation			ССМ		0.5		%
Load Regulation (Note 5)			ССМ		0.5		%
Watch-Dog Res	et						
Watch-Dog Res	et Input	V _{WDT_H}	High level	1.2			V
Voltage		Vwdt_l	Low level			0.4	, v

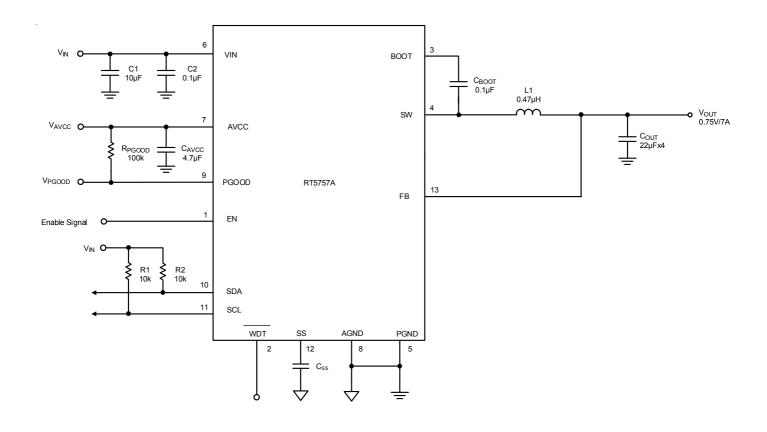


Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
I ² C			1	•		
CDA CCI Input Voltage		High level	1.2			V
SDA, SCL Input Voltage		Low level			0.4	V
Fast Mode						
SCL Clock Rate	f _{SCL}				400	kHz
Hold Time for a Repeated START Condition	thd;sta	After this period, the first clock pulse is generated.	0.6			μS
Low Period of the SCL Clock	tLOW		1.3			μS
High Period of the SCL Clock	thigh		0.6			μS
Set-Up Time for a Repeated START Condition	tsu;sta		0.6			μS
Data Hold Time	t _{HD;DAT}		0		0.9	μS
Data Set-Up Time	tsu;dat		100			ns
Set-Up Time for STOP Condition	tsu;sto		0.6			μS
Bus Free Time between a STOP and a START Condition	t _{BUF}		1.3			μS
Rising Time of Both SDA/SCL Signals	t _r		20		300	ns
Falling Time of Both SDA/SCL Signals	t _f		20		300	ns
SDA/SCL Output Low Sink Current	I _{OL}	SDA voltage = 0.4V	2			mA

- **Note 1.** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2. θ_{JA} is measured under natural convection (still air) at T_A = 25°C with the component mounted on a high effective-thermal-conductivity four-layer test board on a JEDEC 51-7 thermal measurement standard. θ_{JC} is measured at the exposed pad of the package.
- Note 3. Devices are ESD sensitive. Handling precautions are recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.
- Note 5. Guaranteed by design.

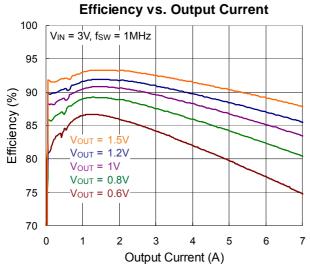


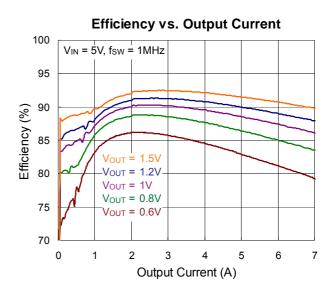
Typical Application Circuit

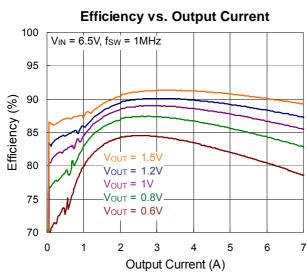


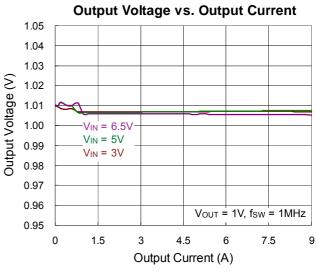


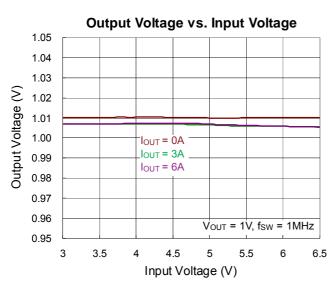
Typical Operating Characteristics

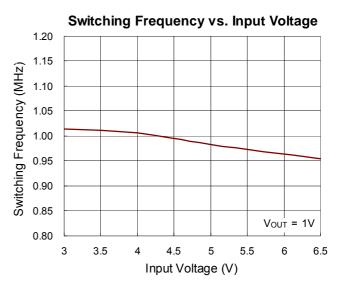




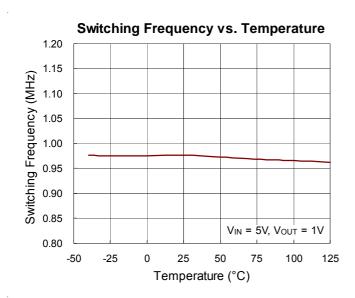


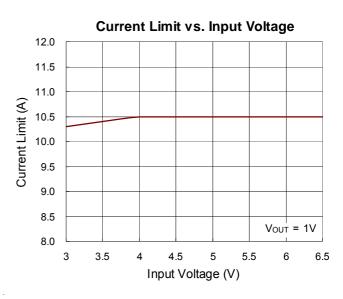


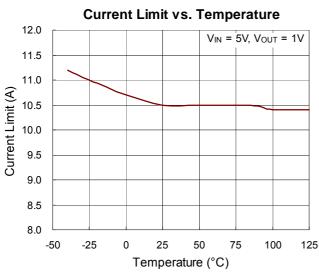


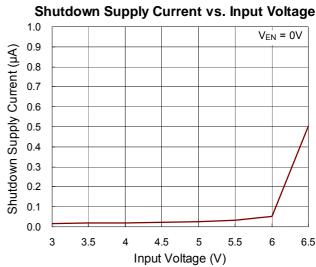


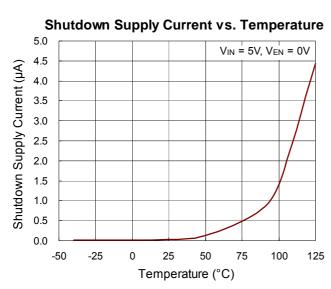


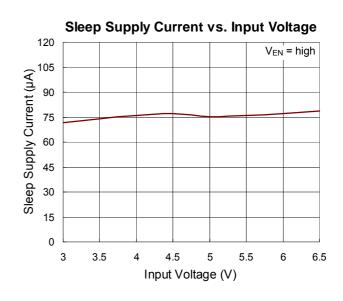




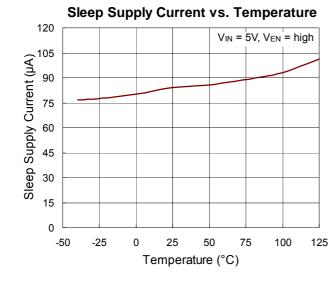


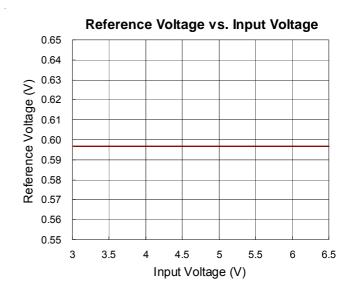


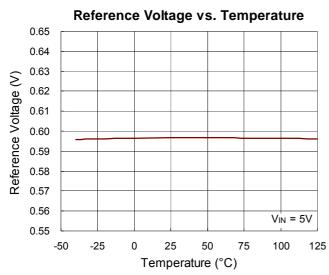


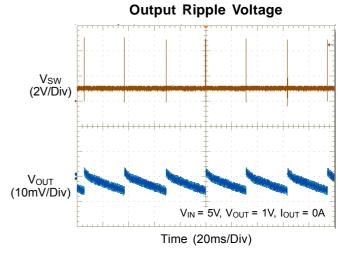


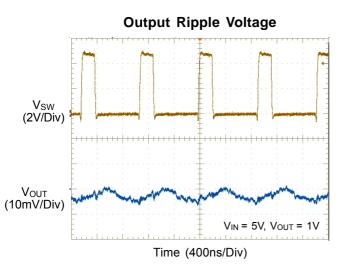


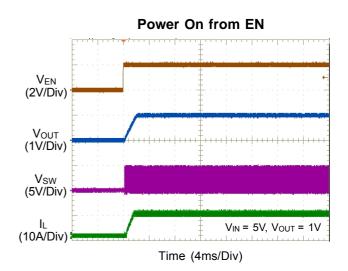




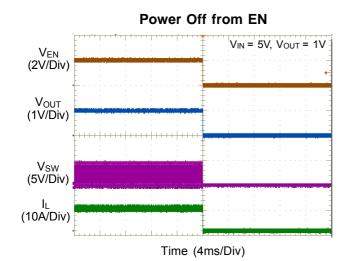


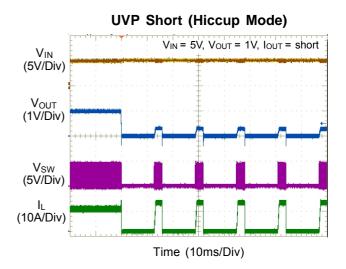














Functional Register Table

Table 1. The RT5757A Register Summary

Name	Туре	Register Reset	Address Offset
MANUFACTURER_ID	R	0x82h	0x00
FREQ_REG	RW	0x0Ah	0x01
SEL_REG	RW	0x28h	0x02
DCDCCTRL_REG	RW	0x0Ah	0x03
STATUS_REG	R	0x00h	0x04
DCDC_SET	RW	0xA4h	0x05

Table 2. MANUFACTURER_ID

Address: 0x Description:		er ID numbe	r register					
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Name		MANUFACTURER_ID						
Reset Value		0x82h						
Read/Write	R	R	R	R	R	R	R	R

Bits	Name	Description
7:0	MANUFACTURER_ ID	Return the manufacturer ID number : 0x82h

Table 3. FREQ_REG

Address: 0x01

Description : Configure register

Set VID change slew rate and PWM frequency.

OCT VID GHAIN	is change siew rate and i with requestoy.							
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Name	Reserved				TS	ГЕР	FR	EQ
Reset Value	0	0	0	0	1	0	1	0
Read/Write	R	R	R	R	R/W	R/W	R/W	R/W

Bits	Name	Description			
7:4	Reserved	Reserved bit			
3:2	TSTEP	TSTEP[3:2] = 00b : 20mV/μs TSTEP[3:2] = 01b : 15mV/μs TSTEP[3:2] = 10b : 10mV/μs (default) TSTEP[3:2] = 11b : 5mV/μs			
1:0	FREQ	FREQ[1:0] = 00b, 0.6MHz FREQ[1:0] = 01b, 0.8MHz FREQ[1:0] = 10b, 1.0MHz (default) FREQ[1:0] = 11b, 1.5MHz			



Table 4. SEL_REG

Address: 0x02 Description: VID setting register								
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Name	Reserved		SEL					
Reset Value	0	0	0	0	1	1	0	0
Read/Write	R	R/W						

Bits	Name	Description
7	Reserved	Reserved bit
6:0	SEL	Supply voltage: SEL[6:0] = 0000000b: 0.6V SEL[6:0] = 0000010b: 0.6125V SEL[6:0] = 0000010b: 0.625V SEL[6:0] = 00000110b: 0.6375V SEL[6:0] = 0000110b: 0.65V SEL[6:0] = 0000110b: 0.665V SEL[6:0] = 0000110b: 0.665V SEL[6:0] = 0000110b: 0.675V SEL[6:0] = 0000110b: 0.675V SEL[6:0] = 0000110b: 0.675V SEL[6:0] = 000110b: 0.707 SEL[6:0] = 0001000b: 0.77V SEL[6:0] = 0001000b: 0.775V SEL[6:0] = 0001010b: 0.725V SEL[6:0] = 0001101b: 0.7375V SEL[6:0] = 0001101b: 0.758V (default) SEL[6:0] = 0001110b: 0.758V (default) SEL[6:0] = 0001110b: 0.775V SEL[6:0] = 0001110b: 0.775V SEL[6:0] = 0001111b: 0.7875V SEL[6:0] = 00010000b: 0.8V SEL[6:0] = 0010001b: 0.8125V SEL[6:0] = 0010001b: 0.825V SEL[6:0] = 0011001b: 0.825V SEL[6:0] = 0011010b: 0.855V SEL[6:0] = 0011011b: 0.8575V SEL[6:0] = 0010111b: 0.8575V SEL[6:0] = 0010111b: 0.9375V SEL[6:0] = 0011111b: 0.9875V SEL[6:0] = 00111001b: 0.9925V SEL[6:0] = 0011101b: 0.9925V SEL[6:0] = 0011101b: 0.9925V SEL[6:0] = 0011111b: 0.99375V SEL[6:0] = 0011111b: 0.99375V SEL[6:0] = 0011111b: 0.9957V SEL[6:0] = 0011111b: 0.9875V SEL[6:0] = 0010001b: 1.055V SEL[6:0] = 0100010b: 1.055V SEL[6:0] = 0100011b: 1.055V SEL[6:0] = 0100011b: 1.055V SEL[6:0] = 0100011b: 1.055V SEL[6:0] = 0100011b: 1.055V



Bits	Name	Description
7	Reserved	Reserved bit
6:0	SEL	Supply voltage: SEL[6:0] = 0101000b: 1.1V SEL[6:0] = 0101001b: 1.1125V SEL[6:0] = 0101010b: 1.125V SEL[6:0] = 0101010b: 1.15V SEL[6:0] = 0101101b: 1.1625V SEL[6:0] = 0101111b: 1.1875V SEL[6:0] = 0101111b: 1.1875V SEL[6:0] = 0110111b: 1.1875V SEL[6:0] = 0110100b: 1.25V SEL[6:0] = 0110000b: 1.25V SEL[6:0] = 0110010b: 1.225V SEL[6:0] = 0110010b: 1.25V SEL[6:0] = 0110010b: 1.25V SEL[6:0] = 0110010b: 1.25V SEL[6:0] = 0110101b: 1.2625V SEL[6:0] = 0110101b: 1.2625V SEL[6:0] = 0110101b: 1.275V SEL[6:0] = 0110110b: 1.275V SEL[6:0] = 0110110b: 1.375V SEL[6:0] = 0110110b: 1.375V SEL[6:0] = 0111010b: 1.3375V SEL[6:0] = 0111110b: 1.3375V SEL[6:0] = 0111110b: 1.3375V SEL[6:0] = 0111110b: 1.3875V SEL[6:0] = 0111110b: 1.3875V SEL[6:0] = 0111110b: 1.3875V SEL[6:0] = 0111111b: 1.3875V SEL[6:0] = 0111111b: 1.3675V SEL[6:0] = 0111111b: 1.3675V SEL[6:0] = 0100000b: 1.4V SEL[6:0] = 1000000b: 1.4V SEL[6:0] = 1000010b: 1.455V SEL[6:0] = 1000010b: 1.455V SEL[6:0] = 1000010b: 1.455V SEL[6:0] = 1000010b: 1.455V SEL[6:0] = 100011b: 1.4875V SEL[6:0] = 100011b: 1.4875V SEL[6:0] = 100011b: 1.525V SEL[6:0] = 100011b: 1.525V SEL[6:0] = 100011b: 1.575V SEL[6:0] = 1000101b: 1.575V SEL[6:0] = 1000101b: 1.575V SEL[6:0] = 1000101b: 1.555V SEL[6:0] = 1001010b: 1.555V SEL[6:0] = 1001010b: 1.555V SEL[6:0] = 1001011b: 1.5625V SEL[6:0] = 1001010b: 1.555V SEL[6:0] = 1001010b: 1.555V SEL[6:0] = 1001010b: 1.555V SEL[6:0] = 1001010b: 1.575V SEL[6:0] = 1001010b: 1.575V SEL[6:0] = 1001010b: 1.655V SEL[6:0] = 1010101b: 1.7725V SEL[6:0] = 1010101b: 1.7725V SEL[6:0] = 1010101b: 1.7725V SEL[6:0] = 1011010b: 1.7725V SEL[



Table 5. DCDCCTRL_REG

Address: 0x03 Description: Discharge resistor enable, PSKIP Mode/PWM control, and internal enable registers									
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
Name		Rese	rved		Discharge	PWM	Enable	Reserved	
Reset Value	0	0	0	0	1	0	1	0	
Read/Write	R	R	R	R	R/W	R/W	R/W	R	

Bits	Name	Description
7 :4	Reserved	Reserved bit
3	Discharge	Discharge[3] = 0b : disable discharge resistor (Only OT/UVLO = 1, disable discharge; EN = 0, enable discharge) Discharge[3] = 1b : enable discharge resistor (default)
2	PWM	PWM[2] = 0b : PSKIP mode (default) PWM[2] = 1b : Force PWM
1	Enable	Enable[1] = 0b : disable Enable[1] = 1b : enable (default)
0	Reserved	Reserved bit

Table 6. STATUS_REG

Address: 0x04 Description: Indication of status									
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
Name		Reserved						UV	
Reset Value	0	0	0	0	0	0	0	0	
Read/Write	R	R	R	R	R	R	R	R	

Bits	Name	Description
7:2	Reserved	Reserved bit
1	ОТ	OT[1] = 0b : no OT OT[1] = 1b : OT
0	UV	UV[0] = 0b : no UV UV[0] = 1b : UV



Table 7. DCDC_SET

Address: 0x05 Description: current limit, thermal shutdown threshold, PGOOD enable delay time, VID								
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Name	OCSET		OTSET		PGDSET		Reserved	
Reset Value	1	0	1	0	0	1	0	0
Read/Write	R	R	R	R/W	R/W	R/W	R/W	R

Bits	Name	Description
7:6	OCSET	OCSET[7:6] = 00b : no POC OCSET[7:6] = 01b : 8A OCSET[7:6] = 10b : 8.8A (default) OCSET[7:6] = 11b : 9.6A
5 : 4	OTSET	OTSET[5:4] = 00b : no OT OTSET[5:4] = 01b : 140°C OTSET[5:4] = 10b : 150°C (default) OTSET[5:4] = 11b : 170°C
3:2	PGDSET	PGDSET[3:2] = 00b : PGOOD enable delay time = $0\mu s$ PGDSET[3:2] = 01b : PGOOD enable delay time = $10\mu s$ (default) PGDSET[3:2] = 10b : PGOOD enable delay time = $20\mu s$ PGDSET[3:2] = 11b : PGOOD enable delay time = $40\mu s$
1:0	Reserved	Reserved bit

Table 8. WDT_EN

Address: 0x42 Description: Watch-dog enable								
Bits	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Name			Rese	erved			WDT_EN	Reserved
Reset Value	0	0	0	0	0	0	0	0
Read/Write	R	R	R	R	R	R	R/W	R

Bits	Name	Description
1	WDT_EN	Enable watch-dog reset function 0: WDT disable (default) 1: WDT enable



Application Information

Richtek's component specification does not include the following information in the Application Information section. Thereby no warranty is given regarding its validity and accuracy. Customers should take responsibility to verify their own designs and reserve suitable design margin to ensure the functional suitability of their components and systems.

Inductor Selection

When designing the output stage of the synchronous buck converter, it is recommended to start with the inductor. However, it may require several iterations because the exact inductor value is generally flexible and is optimized for low cost, small form factor, and high overall performance of the converter. Further, inductors vary with manufacturers in both material and value, and typically have a tolerance of ±20%.

Three key inductor parameters to be specified for operation with the device are inductance (L), inductor saturation current (I_{SAT}), and DC resistance (DCR), which affects performance of the output stage. An inductor with lower DCR is recommended for applications of higher peak current or load current, and it can improve system performance. Lower inductor values are beneficial to the system in physical size, cost, DCR, and transient response, but they will cause higher inductor peak current and output voltage ripple to decrease system efficiency. Conversely, higher inductor values can increase system efficiency at the expense of larger physical size, slower transient response due to the longer response time of the inductor. A good compromise among size, efficiency, and transient response can be achieved by setting an inductor current ripple (ΔI_{\perp}) of about 20% to 50% of the desired full output load current. To meet the inductor current ripple (ΔI_L) requirements, a minimum inductance must be chosen and the approximate inductance can be calculated by the selected input voltage, output voltage, switching frequency (f_{SW}) , and inductor current ripple (ΔI_L) , as below:

$$L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_{L}}$$

Once the inductance is chosen, the inductor ripple current (ΔI_L) and peak inductor current $(I_{L PEAK})$ can be calculated, as below:

$$\Delta I_{L} = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L}$$

$$I_{L_PEAK} = I_{OUT_MAX} + \frac{1}{2} \Delta I_{L}$$

$$I_{L_VALLEY} = I_{OUT_MAX} - \frac{1}{2} \Delta I_{L}$$

where I_{OUT MAX} is the maximum rated output current or the required peak current.

The inductor must be selected to have a saturation current and thermal rating which exceed the required peak inductor current I_{L PEAK}. For a robust design to maintain control of inductor current in overload or short-circuit conditions, some applications may desire inductor saturation current rating up to the switch current limits of the device. However, the built-in output under-voltage protection (UVP) feature makes this unnecessary for most applications.

For best efficiency, a low-loss inductor having the lowest possible DCR that still fits in the allotted dimensions will be chosen. Ferrite cores are often the best choice. However, a shielded inductor, possibly larger or more expensive, will probably give fewer EMI and other noise problems.

The following design example demonstrates the steps to apply the equations defined above. The RT5757A's Typical Application Circuit for output voltage of 0.75V at maximum output current of 7A and an input voltage of 5V with inductor current ripple of 1.75A (i.e. 25%, in the recommended range of 20% to 50%, of the maximum rated output current) is taken as the design example. The approximate minimum inductor value can first be calculated as below:

$$L = \frac{1 \times (5 - 0.75)}{5 \times 1 MHz \times 1.75A} = 0.472 \mu H$$

where f_{SW} is 1MHz. The inductor current ripple will be set at 1.75A, as long as the calculated inductance of 0.472µH is used. However, the inductor of the exact inductance value may not be readily available, and therefore an inductor of a nearby value will be chosen. In this case, 0.47μH

DS5757A-00 September 2023

RT5757A

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inductance is available and actually used in the Typical Application Circuit. The actual inductor current ripple (ΔI_L) and required peak inductor current (I_{L_PEAK}) can be calculated as below :

$$\Delta I_L = \frac{1 \times (5 - 0.75)}{5 \times 1 MHz \times 0.47 \mu H} = 1.8A$$

$$I_{L_PEAK} = I_{OUT_MAX} + \frac{1}{2}\Delta I_{L} = 7 + \frac{1.8}{2} = 7.9A$$

For the $0.47\mu H$ inductance value, the inductor saturation current and thermal rating should exceed 7.9A.

Input Capacitor Selection

Input capacitors are needed to smooth out the RMS ripple current (I_{RMS}) imposed by the switching currents and drawn from the input power source, by reducing the ripple voltage amplitude seen at the input of the converters. The voltage rating of the input filter capacitors must be greater than the maximum input voltage. It is also important to consider the ripple current capabilities of capacitors.

The RMS ripple current (I_{RMS}) of the regulator can be determined by the input voltage (V_{IN}), output voltage (V_{OUT}), and rated output current (I_{OUT}) as the following equation:

$$I_{RMS} = I_{OUT} \times \frac{V_{OUT}}{V_{IN}} \times \sqrt{\frac{V_{IN}}{V_{OUT}}} - 1$$

From the above, the maximum RMS input ripple current occurs at maximum output load, which will be used as the requirements to consider the current capabilities of the input capacitors. Furthermore, for a single-phase buck converter, the duty cycle is approximately the ratio of output voltage to input voltage. The maximum ripple voltage usually occurs at 50% duty cycle, that is, $V_{IN} = 2 \times V_{OUT}$. The maximum I_{RMS} as I_{RMS} (Max), can be approximated as 0.5 x I_{OUT MAX}, where I_{OUT MAX} is the maximum rated output current. Besides, the variation of the capacitance value with temperature, DC bias voltage, switching frequency, and allowable peal-to-peak ripple voltage that reflects back to the input, also needs to be taken into consideration. For example, the capacitance value of a capacitor decreases as the DC bias across the capacitor increases; also, higher switching frequency allows the use of input capacitors of smaller capacitance values.

Ceramic capacitors are most commonly used to be placed right at the input of the converter to reduce ripple voltage

amplitude because only ceramic capacitors have extremely low ESR which is required to reduce the ripple voltage. Note that the capacitors need to be placed as close as to the input pins as possible for highest effectiveness. Ceramic capacitors are preferred also due to their low cost, small size, high RMS current ratings, robust inrush surge current capabilities, and low parasitic inductance, which helps reduce the high-frequency ringing on the input supply.

However, care must be taken when ceramic capacitors are used at the input, and the input power is supplied by a wall adapter, connected through a long and thin wire. When a load step occurs at the output, a sudden inrush current will surge through the long inductive wire, which can induce ringing at the device's power input and potentially cause a very large voltage spike at the VIN pin to damage the device. For applications where the input power is located far from the device input, it may be required that the low-ESR ceramic input capacitors be placed in parallel with a bulk capacitor of other types, such as tantalum, electrolytic, or polymer, to dampen the voltage ringing and overshoot at the input, caused by the long input power path and input ceramic capacitor.

It is suggested to choose capacitors with higher temperature ratings than required. Several ceramic capacitors may be parallel to meet application requirements, such as the RMS current, size, and height. The Typical Application Circuit can use one $10\mu F$ and one high-frequency- noise-filtering $0.1\mu F$ low-ESR ceramic capacitors at the input.

Output Capacitor Selection

Output capacitance affects the output voltage of the converter, the response time of the output feedback loop, and the requirements for output voltage sag and soar. The sag occurs after a sudden load step current applied, and the soar occurs after a sudden load removal. Increasing the output capacitance reduces the output voltage ripple and output sag and soar, while it increases the response time that the output voltage feedback loop takes to respond to step loads. Therefore, there is a tradeoff between output capacitance and output response. It is recommended to choose a minimum output capacitance to meet the output voltage requirements of the converter, and have a quick



transient response to step loads.

The ESR of the output capacitor affects the damping of the output filter and the transient response. In general, low-ESR capacitors are good choices due to their excellent capability in energy storage and transient performance. The RT5757A, therefore, is specially optimized for ceramic capacitors. Consider also DC bias and aging effects while selecting the output capacitor.

Output Voltage Ripple

The output voltage ripple at the switching frequency is a function of the inductor current ripple going through the output capacitor's impedance. To derive the output voltage ripple, the output capacitor with capacitance, C_{OUT}, and its equivalent series resistance, RESR, must be taken into consideration. The output peak-to-peak ripple voltage ΔV_{P-P} , caused by the inductor current ripple ΔI_L , is characterized by two components, which are ESR ripple ΔV_{P-P} ESR and capacitive ripple ΔV_{P-P} C; they can be expressed as below:

$$\begin{split} &\Delta V_{P-P} = \Delta V_{P-P_ESR} + \Delta V_{P-P_C} \\ &\Delta V_{P-P_ESR} = \Delta I_L \times R_{ESR} \\ &\Delta V_{P-P_C} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}} \end{split}$$

If ceramic capacitors are used as the output capacitors, both the components need to be considered due to the extremely low ESR and relatively small capacitance.

For the RT5757A's Typical Application Circuit for output voltage of 0.75V, and actual inductor current ripple (ΔI_L) of 1.8A, using four paralleled 22µF ceramic capacitors with ESR of about $5m\Omega$ as output capacitors; the two output ripple components are as below:

$$\begin{split} \Delta V_{P-P_ESR} &= \Delta I_L \times R_{ESR} = 1.8A \times 5 m\Omega = 9 mV \\ \Delta V_{P-P_C} &= \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}} = \frac{1.8A}{8 \times 88 \mu F \times 1 MHz} \\ &= 2.56 mV \end{split}$$

$$\Delta V_{P-P} = \Delta V_{P-P_ESR} + \Delta V_{P-P_C} = 11.56 \text{mV}$$

Output Transient Undershoot and Overshoot

In addition to the output voltage ripple at the switching frequency, the output capacitor and its ESR also affect output voltage sag, which is undershoot on a positive load step, and output voltage soar, which is overshoot on a negative load step. With the built-in ACOT® architecture,

the IC can have very fast transient responses to the load steps and small output transients.

However, the combination of a small ceramic output capacitor (that is, of little capacitance) and a low output voltage (that is, only little charge stored in the output capacitor), used in low-duty-cycle applications (which require high inductance to get reasonable ripple currents for high input voltages), causes an increase in the size of voltage variations (i.e. sag/soar) in response to very quick load changes. Typically, the load changes slowly, compared with the IC's switching frequency. However, for presentday applications, more and more digital blocks may exhibit nearly instantaneous large transient load changes. Therefore, in the following section, how to calculate the worst-case voltage swings in response to very fast load steps will be explained in details.

Both of the output transient undershoot and overshoot have two components: a voltage step caused by the output capacitor's ESR, and a voltage sag or soar due to the finite output capacitance and the inductor current slew rate. The following formulas can be used to check if the ESR is low enough (which is usually not a problem with ceramic capacitors) and if the output capacitance is large enough to prevent excessive sag or soar on very fast load steps, with the chosen inductor value.

The voltage step ($\Delta V_{OUT\ ESR}$) caused by the ESR is a function of the load step (ΔI_{OUT}) and the ESR (R_{ESR}) of the output capacitor, described as below:

$$\Delta V_{OUT_ESR} = \Delta I_{OUT} \times R_{ESR}$$

The voltage amplitude ($\Delta V_{OUT\ SAG}$) of the capacitive sag is a function of the load step (ΔI_{OUT}), the output capacitor value (C_{OUT}), the inductor value (L), the input-to-output voltage differential, and the maximum duty cycle (D_{MAX}). And, the maximum duty cycle during a fast transient can be determined by the on-time (toN) and the minimum offtime (t_{OFF MIN}) since the ACOT[®] control scheme will ramp the current during on-times, which are spaced apart by a minimum off-time, that is, as fast as allowed. The approximate on-time (neglecting parasitics) and maximum duty cycle for a given input and output voltage can be calculated according to the following equations:

$$t_{ON}$$
 = $\frac{V_{OUT}}{V_{IN} \times f_{SW}}$ and D_{MAX} = $\frac{t_{ON}}{t_{ON} + t_{OFF_MIN}}$



Note the actual on-time will be slightly larger than the calculated one as the IC will automatically adapt to compensate the internal voltage drops, such as the voltage across high-side switch due to on-resistance. However, both of these can be ignore since the on-time increase can compensate for the voltage drops. The output voltage sag ($\Delta V_{OUT-SAG}$) can then be calculated as below:

$$\Delta V_{OUT_SAG} = \frac{L \times (\Delta I_{OUT})^2}{2 \times C_{OUT} \times (V_{IN} \times D_{MAX} - V_{OUT})}$$

The voltage amplitude of the capacitive soar is a function of the load step (ΔI_{OUT}), the output capacitor value (C_{OUT}), the inductor value (L), and the output voltage (V_{OUT}). And the output voltage soar (ΔV_{OUT_SOAR}) can be calculated as below :

$$\Delta V_{OUT_SOAR} = \frac{L \times (\Delta I_{OUT})^2}{2 \times C_{OUT} \times V_{OUT}}$$

EN Pin for Start-Up and Shutdown Operation

For automatic start-up, the EN pin, with normal voltage rating, can be connected to the input supply V_{IN} , through a $100 k\Omega$ resistor. The large built-in hysteresis band makes the EN pin useful for simple delay and timing circuits. The EN pin can be externally connected to V_{IN} by adding a resistor R_{EN} and a capacitor C_{EN} , as shown in Figure 1, to have an additional delay. The time delay can be calculated with the EN's internal threshold, at which switching operation begins.

An external MOSFET can be added for the EN pin to be logic-controlled, as shown in Figure 2. In this case, a $100 k\Omega$ pull-up resistor, R_{EN} , is connected between V_{IN} and the EN pin. The MOSFET Q1 will be under logic control to pull down the EN pin. To prevent the device being enabled when V_{IN} is smaller than the V_{OUT} target level or some other desired voltage level, a resistive divider (R_{EN1} and R_{EN2}) can be used to externally set the input undervoltage lockout threshold, as shown in Figure 3.

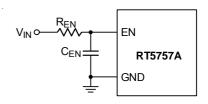


Figure 1. Enable Timing Control

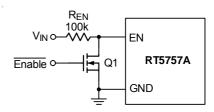


Figure 2. Logic Control for the EN Pin

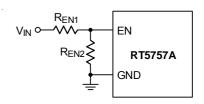


Figure 3. Resistive Divider for Under-Voltage Lockout
Threshold Setting

Output Voltage Programming

The output voltage can be set by I²C interface after the soft-start is finished.

The output voltage can be selected from Table 4. SEL REG.

External Bootstrap Diode

A bootstrap capacitor of $0.1\mu F$ low-ESR ceramic capacitor is connected between the BOOT and SW pins to supply the high-side gate driver. It is recommended to add an external bootstrap diode between an external 5V voltage supply and the BOOT pin to improve enhancement of the internal MOSFET switch and improve efficiency when the input voltage is below 5.5V. The bootstrap diode can be a low-cost one, such as 1N4148 or BAT54.



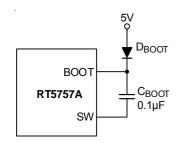


Figure 4. External Bootstrap Diode

Resistor at BOOT Pin

The gate driver of an internal power MOSFET, utilized as a high-side switch, is optimized for turning on the switch not only fast enough for reducing switching power loss, but also slow enough for minimizing EMI. The EMI issue is worse when the switch is turned on rapidly due to high di/dt noises induced. When the high-side switch is being turned off, the SW node will be discharged relatively slowly by the inductor current due to the presence of the dead time when both the high-side and low-side switches are turned off.

In some cases, it is desirable to reduce EMI further, even at the expense of some additional power dissipation. The turn-on rate of the high-side switch can be slowed by placing a small (< 47Ω) resistor between the BOOT pin and the external bootstrap capacitor. This will slow down the rates of the high-side switch turn-on and the rise of Vsw. The recommended application circuit is shown in Figure 5, which includes an external bootstrap diode for charging the bootstrap capacitor and a bootstrap resistor $R_{\rm BOOT}$ being placed between the BOOT pin and the capacitor/diode connection.

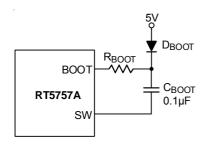


Figure 5. External Bootstrap Diode and Resistor at the BOOT Pin

Soft-Start Function

The RT5757A provides an adjustable soft-start function. The soft-start function is used to prevent large inrush current while the converter is being powered-up. The soft-start time is defined as the output voltage rising time from 10% to 90% of settled level and can be programmed by the external soft-start capacitor C_{SS} between the SS and GND pins. An internal current source I_{SS} (typically, $10\mu A$) charges the capacitor to build a soft-start ramp voltage. The FB voltage will track the ramp voltage of the SS pin during soft-start. The typical soft-start time can be calculated as follows :

Soft-Start Time

$$t_{SS} (ms) = \frac{C_{SS}(nF) \times V_{OUT} \times 0.8}{I_{SS}(\mu A)} = \frac{C_{SS}(nF) \times V_{OUT} \times 0.8}{10(\mu A)}$$

If the SS pin is left unconnected, the soft-start time has its minimum value. Only connect an external soft-start capacitor C_{SS} when longer soft-start time is needed.

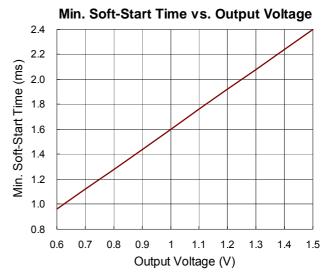


Figure 6. Min. Soft-Start Time vs. Output Voltage

RT5757A



Power-Good Output

The PGOOD pin is an open-drain power-good indication output and is to be connected to an external voltage source through a pull-up resistor. The power-good function is activated after soft-start is finished and is controlled by the feedback signal V_{FB}. During soft-start, PGOOD is actively held low and only allowed to transition high after soft-start is over. If V_{FB} rises above a power-good threshold (V_{TH PGLH}) (typically 95% of the target value), the PGOOD pin will be in high impedance and V_{PGOOD} will be held high after a certain delay elapsed. When V_{FB} drops by a powergood hysteresis (ΔV_{TH_PGLH}) (typically 5% of the target value) or exceeds V_{TH PGHL} (typically 110% of the target value), the PGOOD pin will be pulled low. For V_{FB} above V_{TH_PGHL}, V_{PGOOD} will be pulled high again when V_{FB} drops back by a power-good hysteresis ($\Delta V_{TH\ PGHL}$) (typically 5% of the target value). Once being started-up, if any internal protection is triggered, PGOOD will be pulled low to GND.

Output Under-Voltage Protection (Hiccup Mode)

The RT5757A includes output under-voltage protection (UVP) against over-load or short-circuited condition by constantly monitoring the feedback voltage V_{FB} . If V_{FB} drops below the under-voltage protection trip threshold (typically 70% of the internal reference voltage), the UV comparator will go high to turn off both the internal high-side and low-side MOSFET switches.

If the output under-voltage condition continues for a period of time, the RT5757A will enter output under-voltage protection with hiccup mode. During hiccup mode, the device remains shut down. After a period of time, a soft-start sequence for auto-recovery will be initiated. Upon completion of the soft-start sequence, if the fault condition is removed, the converter will resume normal operation; otherwise, such cycle for auto-recovery will be repeated until the fault condition is cleared. Hiccup mode allows the circuit to operate safely with low input current and power dissipation, and then resume normal operation as soon as the over-load or short-circuit condition is removed.

Low-Side Current-Limit Protection

The RT5757A features a cycle-by-cycle valley-type current limit protection, measuring the inductor current through the synchronous rectifier (low-side switch). The inductor current level is determined by measuring the low-side switch voltage between the SW pin and GND, which is proportional to the switch current, during the low-side ontime. For greater accuracy, temperature compensation is added to the voltage sensing. Once the current rises above the low-side switch valley current limit (I_{LIM}), the on-time one-shot will be inhibited until the inductor current ramps down to the current limit level (I_{LIM}), that is, another ontime can only be triggered when the inductor current goes below the low-side current limit. This function can prevent the average output current from greatly exceeding the quaranteed low-side current limit value.

If the output load current exceeds the available inductor current (clamped by the above-mentioned low-side current limit), the output capacitor needs to supply the extra current such that the output voltage will begin to drop. If it drops below the output under-voltage protection trip threshold, the IC will stop switching to avoid excessive heat.

I²C Interface

A general-purpose serial interface to control and monitor the configuration registers is provided in the RT5757A and the I^2C slave address of the RT5757A will be 0x62. This I^2C interface supports standard slave mode (100kbps) and fast mode (400kbps). A multiple bytes reading or writing over the I^2C interface can also be done through the RT5757A (see Figure 7).

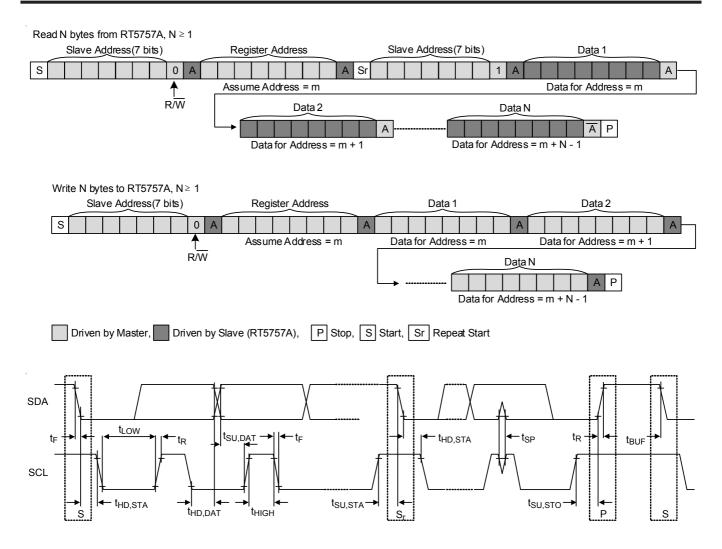


Figure 7. I²C Read/Write Stream and Timing Diagram



Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a UQFN-13L 3x3 (FC) package, the thermal resistance, θ_{JA} , is 38.1°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at T_A = 25°C can be calculated as below:

 $P_{D(MAX)}$ = (125°C - 25°C) / (38.1°C/W) = 2.62W for a UQFN-13L 3x3 (FC) package.

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curves in Figure 8 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

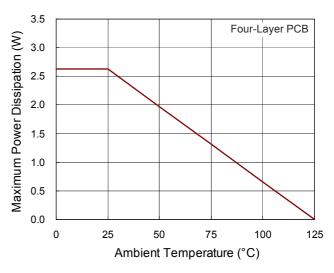


Figure 8. Derating Curve of Maximum Power Dissipation



Layout Consideration

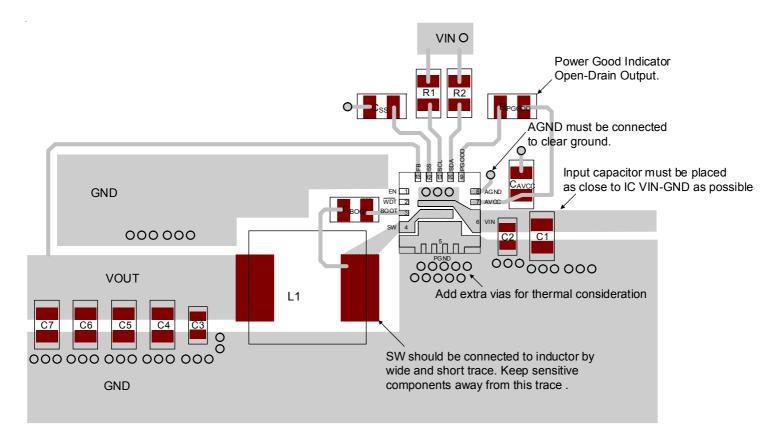


Figure 9. PCB Layout Guide (Top Layer)



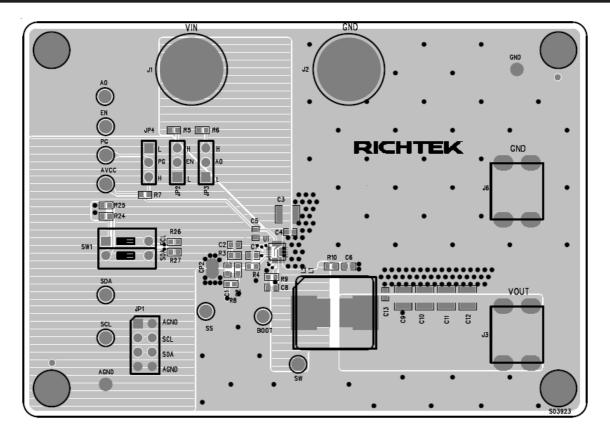


Figure 10. Top Layer PCB Layout

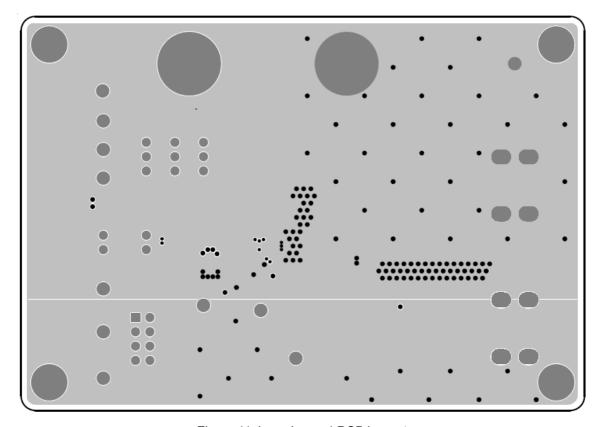


Figure 11. Inner Layer 1 PCB Layout

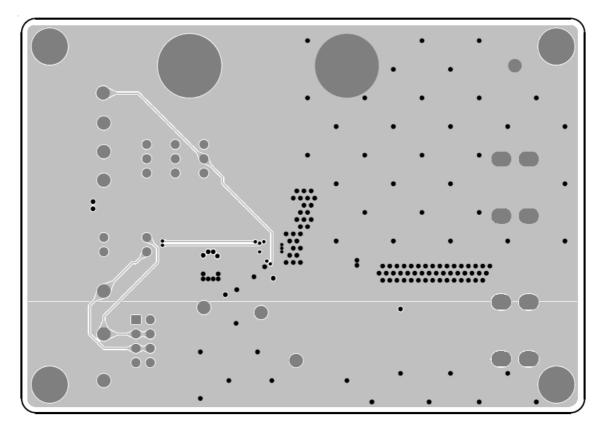


Figure 12. Inner Layer 2 PCB Layout

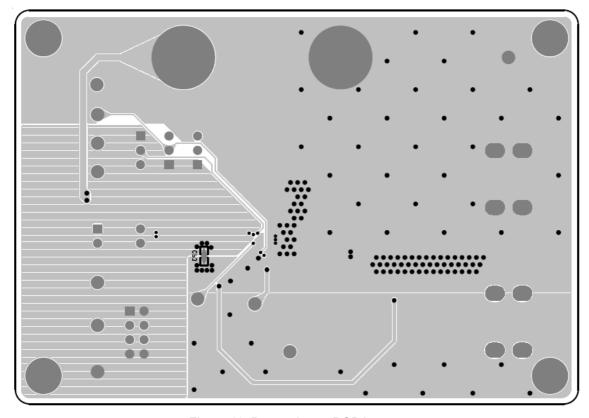


Figure 13. Bottom Layer PCB Layout



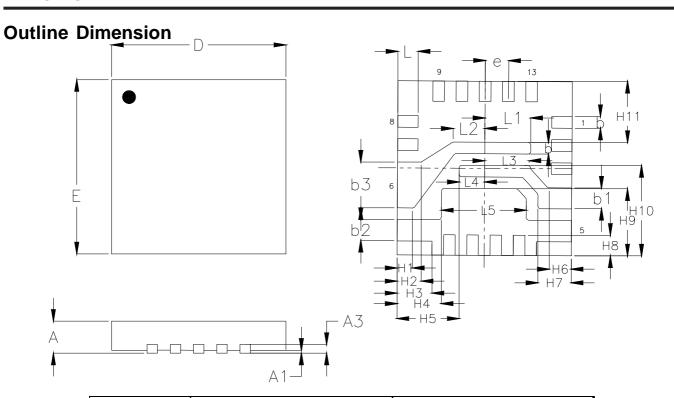
Suggested Inductors for Typical Application Circuit

Component Supplier	Part No.	Inductance (μH)	DCR (m Ω)	Dimensions (mm)
WE	744314047	0.47	1.35	7.0 x 7.0 x 5.0

Recommended Component Selection for Typical Application Circuit

Component Supplier	Part No.	Capacitance (μF)	Case Size	
MURATA	GRM32ER71H106KA12L	10	1210	
TDK	C3225X5R1E226MT	22	1210	
MURATA	GRM188R61C475KAAJ	4.7	0603	



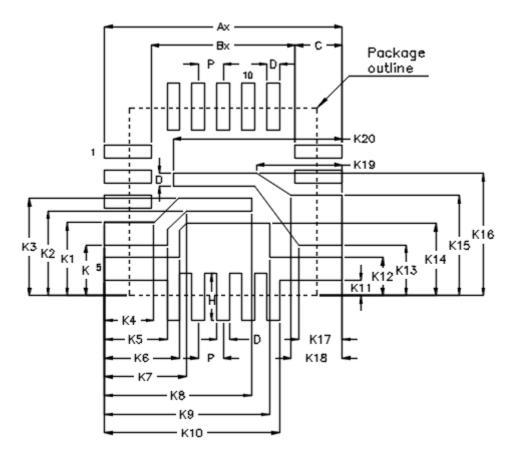


Symbol	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min	Max	Min	Max		
Α	0.500	0.600	0.020	0.024		
A1	0.000	0.050	0.000	0.002		
A3	0.100	0.200	0.004	0.008		
b	0.150	0.250	0.006	0.010		
b1	0.310	0.410	0.012	0.016		
b2	0.320	0.420	0.013	0.017		
b3	0.740	0.840	0.029	0.033		
D	2.900	3.100	0.114	0.122		
E	2.900	3.100	0.114	0.122		
е	0.4	400	0.	016		
L	0.300	0.400	0.012	0.016		
L1	0.740	0.840	0.029	0.033		
L2	0.480	0.580	0.019	0.023		
L3	0.740	0.840	0.029	0.033		
L4	0.390	0.490	0.015	0.019		
L5	1.410	1.510	0.056	0.059		
H1	0.2	280	0.	011		
H2	0.4	420	0.	017		
H3	0.0	600	0.	024		
H4	0.	750	0.030			
H5	1.0	050	0.	041		
H6	0.4	400	0.016			
H7	0.0	600	0.024			
H8	0.3	350	0.014			
H9	1.	150	0.045			
H10	1.9	550	0.061			
H11	1.0	050	0.	041		

U-Type 13L QFN 3x3 (FC) Package



Footprint Information

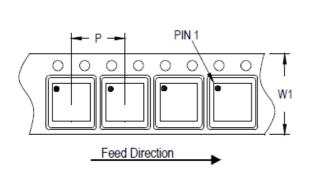


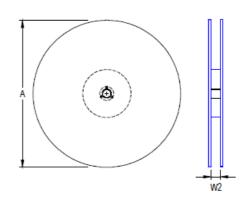
Package	Number of Pin		Footprint Dimension (mm)						Tolerance		
UQFN3x3-13(FC) 13		Р	Ax	Bx	С	D	K	K1	K2	K3	±0.05
		0.40	3.80	2.30	0.75	0.20	0.80	1.17	1.35	1.55	
	12	K4	K5	K6	K7	K8	K9	K10	K11	K12	
	13	0.80	1.00	1.20	1.30	2.35	2.65	2.80	0.24	0.61	
		K13	K14	K15	K16	K17	K18	K19	K20	Н	
		0.80	1.15	1.60	1.95	0.68	0.82	1.37	2.70	0.75]

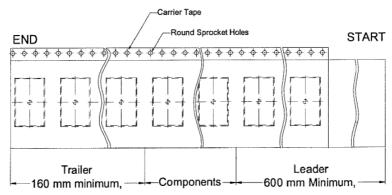


Packing Information

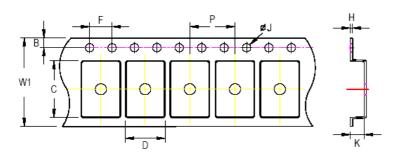
Tape and Reel Data







Package Type	Tape Size	Pocket Pitch	Reel Size (A)		Units	Trailer	Leader	Reel Width (W2)	
r dendge rype	(W1) (mm)	(P) (mm)	(mm)	(in)	per Reel	(mm)	(mm)	Min./Max. (mm)	
QFN/DFN 3x3	12	8	180	7	1,500	160	600	12.4/14.4	



C, D and K are determined by component size.

The clearance between the components and the cavity is as follows:

- For 12mm carrier tape: 0.5mm max.

Tape Size	W1	Р		В		F		Ø١		Н
Tape Size	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm



Tape and Reel Packing

Step	Photo / Description	Step	Photo / Description
1	Reel 7"	4	3 reels per inner box Box A
2	HIC & Desiccant (1 Unit) inside	5	12 inner boxes per outer box
3	Caution label is on backside of Al bag	6	Outer box Carton A

Container	R	teel			Вох			Carton			
Package	Size	Units	Item	Size(cm)	Weight(Kg)	Reels	Units	Item	Size(cm)	Boxes	Unit
OFN 6 DEN 6:0	7"	4 500	Box A	18.3*18.3*8.0	0.1	3	4,500	Carton A	38.3*27.2*38.3	12	54,000
QFN & DFN 3x3	7 1,500	Box E	18.6*18.6*3.5	0.03	1	1,500	ı	For Combined or Pa	artial Reel.		

RT5757A



Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω /cm ²	10 ⁴ to 10 ¹¹					

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Datasheet Revision History

Version	Date	Description	Item
00	2023/9/11	Final & modify	General Description on P1 Features on P1 Ordering Information on P1 Functional Pin Description on P3 Functional Block Diagram on P4 Typical Application Circuit on P10 Application Information on P20, 21, 22, 23, 24, 25, 26, 27, 28, 29, 30